

## MRF6V14300HSR5 Information

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

### General Information

Parameter	Value
Part Number	MRF6V14300HSR5
Description	Pulse Lateral N-Channel RF Power MOSFET, 1400 MHz, 330 W, 50 V
Product Line	614300HS
PTI	RGMA
Material Type	Tested Packaged Device
<a href="#">Life Cycle Description (code)</a>	PRODUCT MATURITY/SATURATION
Status	Active
<a href="#">Application/Qualification Tier</a>	10-YEARS APPLICATION LIFE

### Package Information

Parameter	Value
Package Type and Termination Count	Air Cavity 3
Package Description and Mechanical Drawing	<a href="#">NI-780S</a>
Device Weight(g)	3.27290
Package Length (nominal)(mm)	20.570
Package Width (nominal)(mm)	9.780
Package Thickness (nominal)(mm)	3.760
Tape & Reel	Yes

### Environmental and Compliance Information

Parameter	Value
<a href="#">Pb-Free</a>	
<a href="#">RoHS Compliant</a>	
<a href="#">Halogen Free</a>	Yes
<a href="#">Material Composition Declaration (MCD)</a>	<a href="#">Download MCD Report</a>  <a href="#">Download MCD Report</a> 
<a href="#">RoHS Certificate of Analysis (CoA)</a>	<a href="#">Contact Us</a>
<a href="#">2nd Level Interconnect</a>	e4
Peak Package Body Temperature (PPT)(°C)	260
Maximum Time at Peak Temperature (s)	40
Number of Reflow Cycles	3
REACH SVHC	<a href="#">Freescale REACH Statement</a>

### Manufacturing Information

Parameter	Value
Micron Size(?m)	6

### Ordering Information

Parameter	Value
Minimum Package Quantity (MPQ)	50
MPQ Container	REEL
Exempt from Minimum Delivery Value	Yes
Preferred Order Quantity (POQ)	50
POQ Container	BOX
Leadtime (weeks)	18
Export Control Classification Number (US)	EAR99
Harmonized Tariff (US) <a href="#">Disclaimer</a>	8541.29.0075
CCATS Document	-
ENC Status	-
Other Trade Compliance Documents	-
<a href="#">Budgetary Price excluding tax(US\$)</a> <a href="#">Change Currency</a>	-
Order	

### Product/Process Change Notice (PCN)

Number	Type	Title	Issue Date	Effectivity Date
13811	Product Change Notice	<a href="#">Reduction in Gold Plating Thickness for RF Power Transistor Products</a>	15 Dec 2009	01 Apr 2010
13952	Product Change Notice	<a href="#">RF Power Transistor Internal Matching Capacitor Wafer Fab Transfer</a>	15 Dec 2009	15 Mar 2010
13618	Product Change Notice	<a href="#">RF High Power LDMOS - Additional Assembly and Test Site</a>	28 May 2009	26 Aug 2009
13328	Product Change Notice	<a href="#">Planned LDMOS Fab Transfer</a>	12 Nov 2008	10 Feb 2009

### Operating Characteristics

Parameter	Value
Class	AB
Die Technology	LDMOS
Efficiency (Typ) (%)	60.5
Freq (Max) (MHz)	1400
Freq (Min) (MHz)	1200
Frequency (Max) (MHz)	1400
Frequency Band (Min-Max) (MHz)	1200 to 1400
Matching	I/O
Output Power (Typ) (W) @ Intermodulation Level at Test Signal	330 @ Peak
P1dB (Typ) (W)	330
Power Gain (Typ) (dB) @ f (MHz)	18 @ 1400
Sample Exception Availability	N
Supply Voltage (Typ) (V)	50
Test Signal	Pulse
Thermal Resistance (Spec) (°C/W)	0.13

[Reliability Data Lookup](#)